

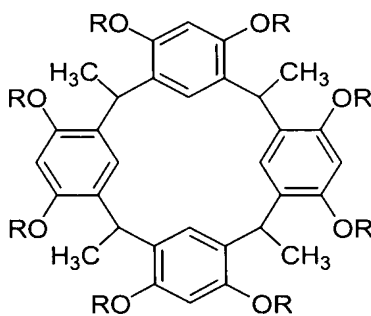
IN THE CLAIMS

Please amend the claims as follows:

Claims 1-17 (Canceled).

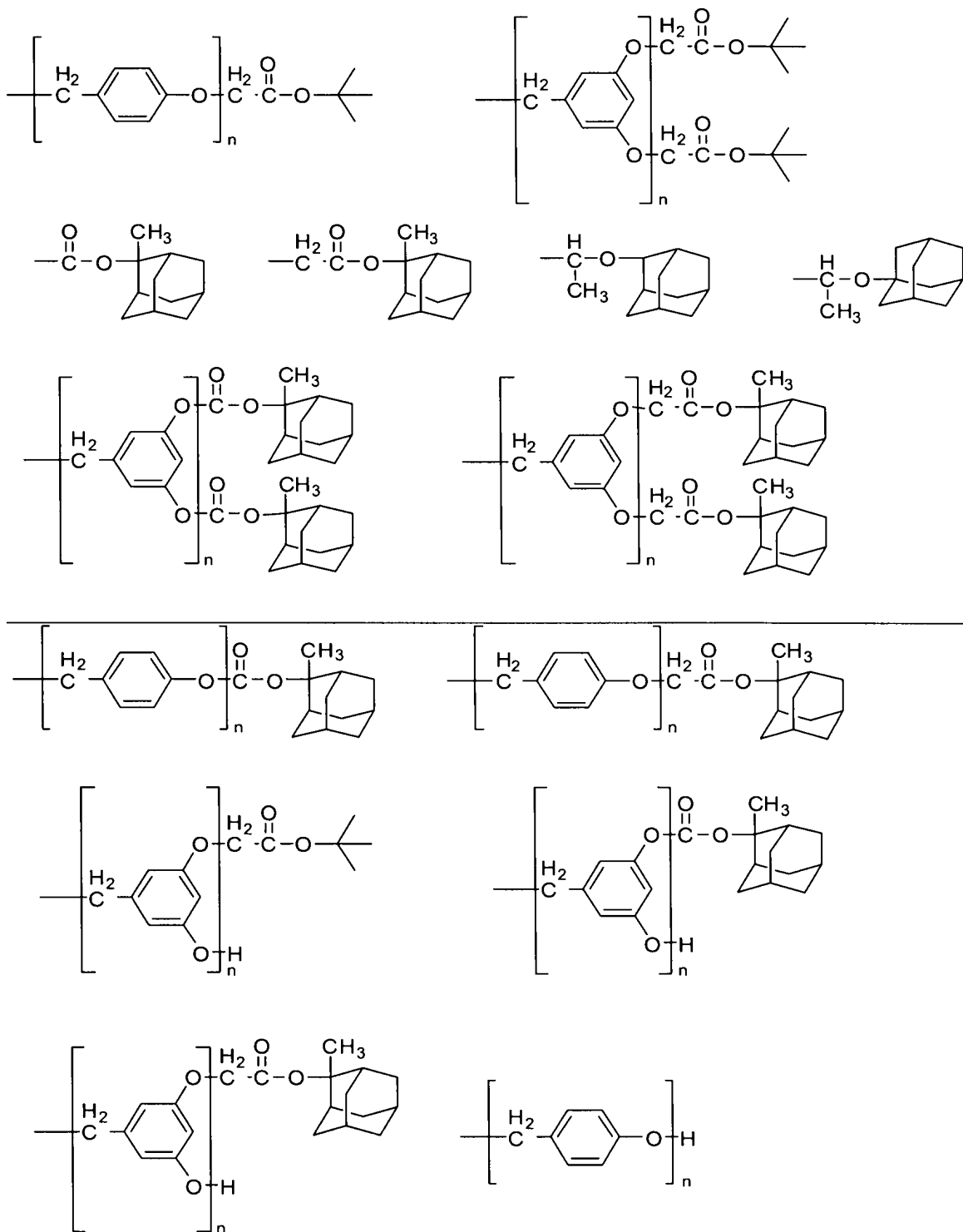
Claim 18 (Currently Amended): A calixresorcinarene compound shown by formula

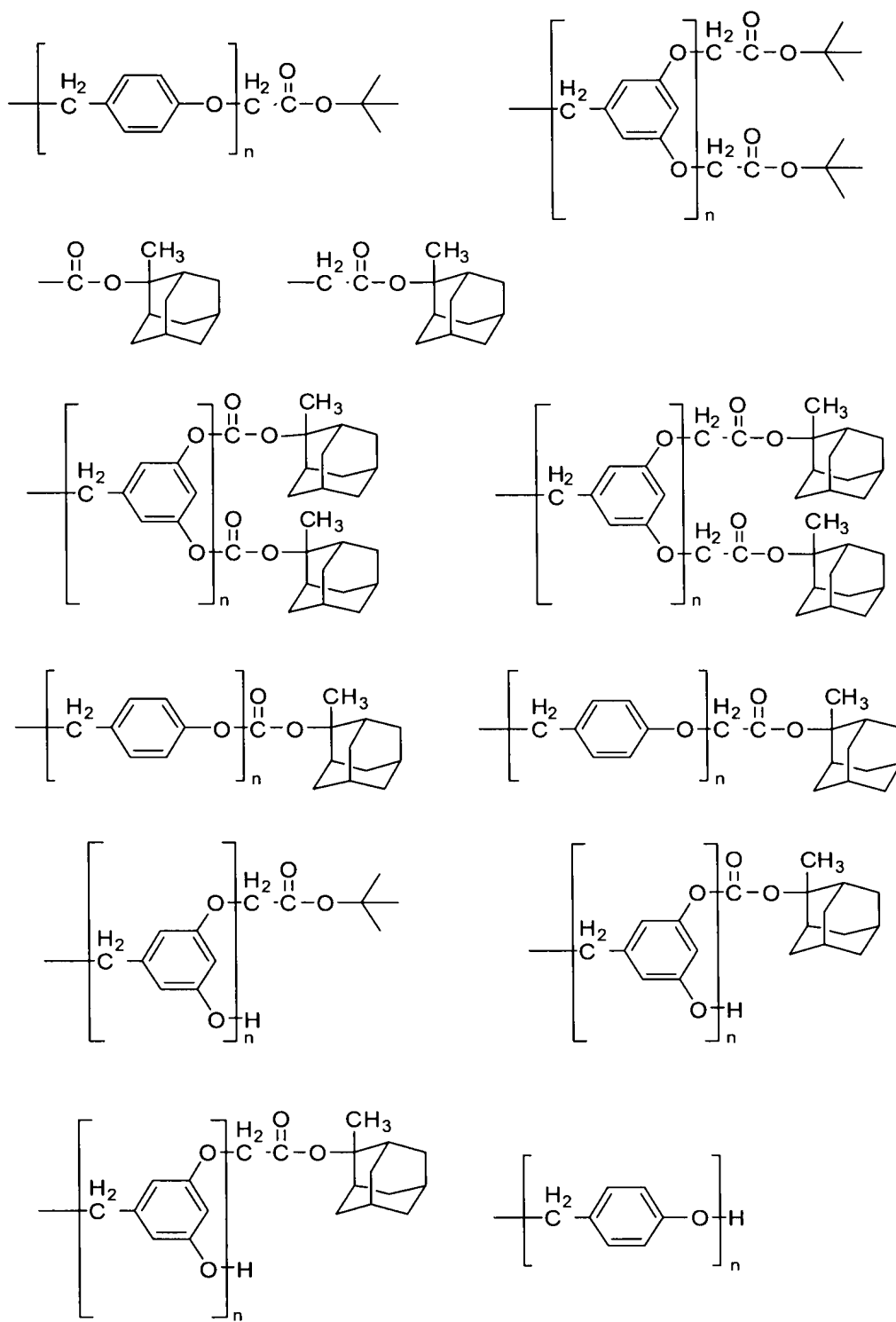
(1),



(1)

wherein R individually represents a hydrogen atom, a 1-tetrahydropyranyl group, a 1-tetrahydrofuranyl group, or one or more organic groups selected from the group consisting of the organic groups shown by the following formulas,





wherein n individually represents an integer of 1 to 50,

provided that a compound in which R is selected only from a hydrogen atom, a 1-tetrahydropyranyl group and a 1-tetrahydrofuranyl group is excluded.

Claim 19 (Previously Presented): A method for the purification of a calixresorcinarene compound according to claim 18 comprising washing said compound with an acidic aqueous solution and processing the washed compound with an ion-exchange resin.

Claim 20 (Previously Presented): A photoresist base material for extreme ultraviolet radiation and/or an electron beam comprising the calixresorcinarene compound according to claim 18 and shown by formula (1).

Claim 21 (Previously Presented): A photoresist composition for extreme ultraviolet radiation and/or an electron beam comprising the photoresist base material according to claim 20 and a solvent.

Claim 22 (Previously Presented): The photoresist composition according to claim 21, further comprising a photoacid generator.

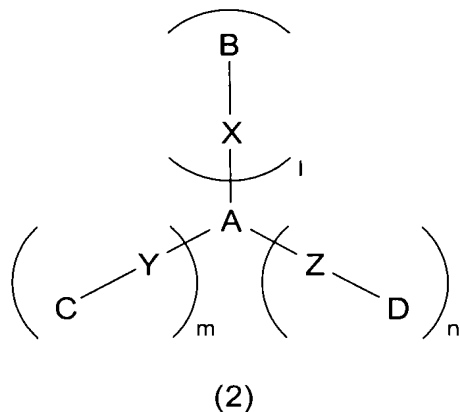
Claim 23 (Previously Presented): The photoresist composition according to claim 21, further comprising a basic organic compound as a quenching agent.

Claims 24-32 (Cancelled).

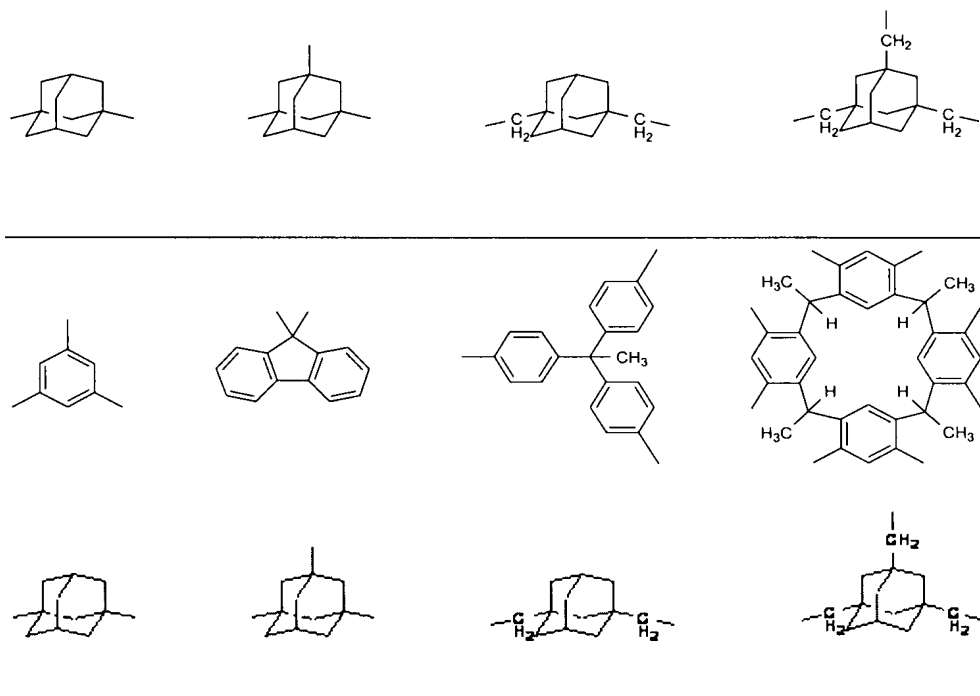
Claim 33 (Previously Presented): A method for microfabrication by lithography using the photoresist composition according to claim 21.

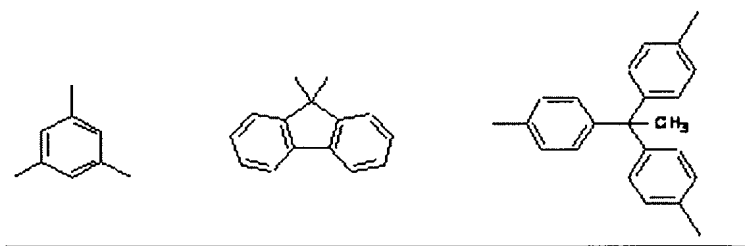
Claim 34 (Previously Presented): A semiconductor device prepared using the photoresist composition according to claim 21.

Claim 35 (Currently Amended): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,

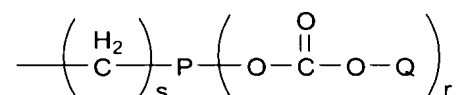


wherein A is an organic group represented by any of the following formulas,

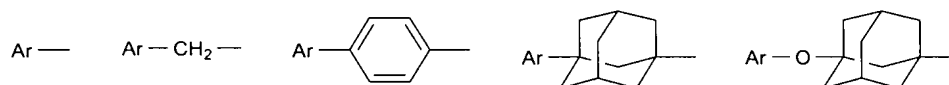




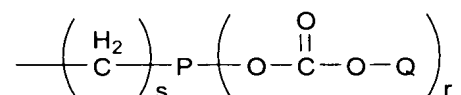
B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, an organic group shown by the formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



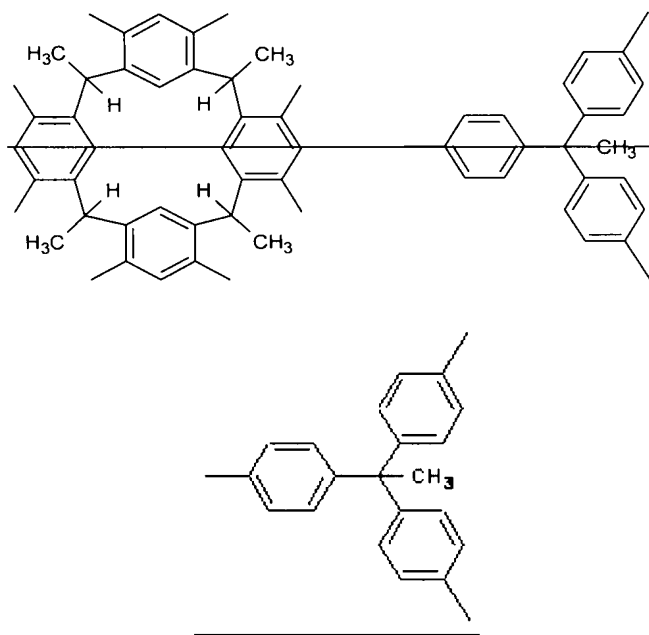
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, ~~and~~

X, Y, and Z individually represent a single bond or an ether bond, and

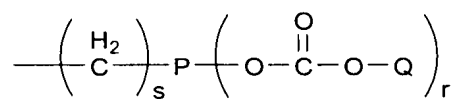
$$1 + m + n = 2 \text{ or } 3.$$

Claim 36 (Previously Presented): The photoresist composition according to claim 35, wherein the extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room temperature and the average diameter of the molecule is 2 nm or less.

Claim 37 (~~Previously Presented~~ Currently Amended): The photoresist composition according to claim 35, wherein A is ~~any one of the organic groups-group~~ represented by the following ~~formulas~~ formula,



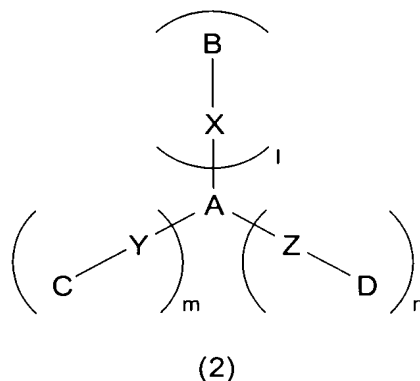
B, C, and D are individually a hydrogen atom, a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



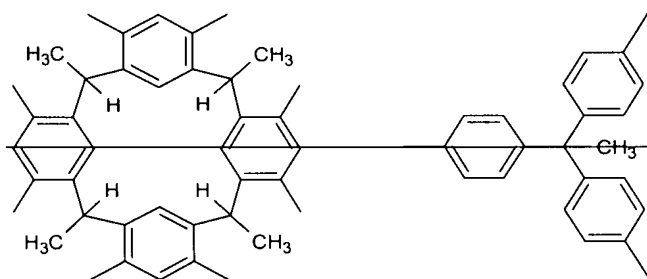
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1),  
 Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is  
 an integer of 0 to 10, and

X, Y, and Z are ether bonds.

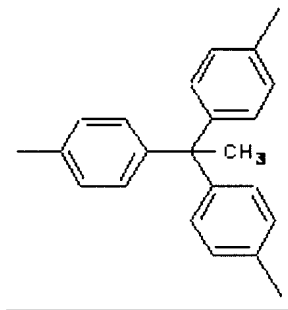
Claim 38 (Currently Amended): A photoresist composition comprising a photoresist  
 base material that is a radiation-reactive organic compound shown by formula (2), obtained  
 by washing with an acidic aqueous solution and processing with an ion-exchange resin, a  
 photoacid generator or a photobase generator, and a quenching agent,



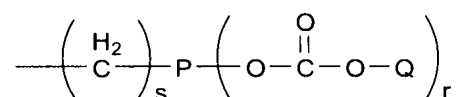
wherein A is an organic group represented by one of the following ~~formulas~~formula,







B, C, and D are individually a tert-butoxycarbonylmethyl group, tert-butoxycarbonyl group, or an organic group shown by formula,

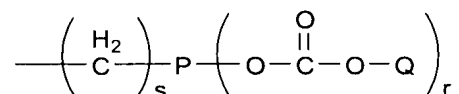


wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

X, Y, and Z individually represent a single bond or an ether bond, and

$$1 + m + n = 3 \text{ or } 8.$$

Claim 39 (Previously Presented): The photoresist composition according to claim 38, wherein the organic group shown by the following formula,



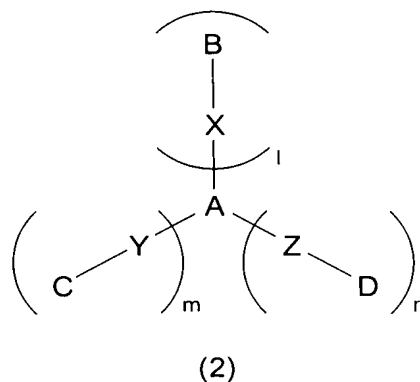
is a 4-(tert-butoxycarbonyloxy)benzyl group or a 3,5-di(tert-butoxycarbonyloxy)benzyl group.

Claim 40 (Previously Presented): The photoresist composition according to claim 38, wherein the radiation is extreme ultraviolet radiation or an electron beam.

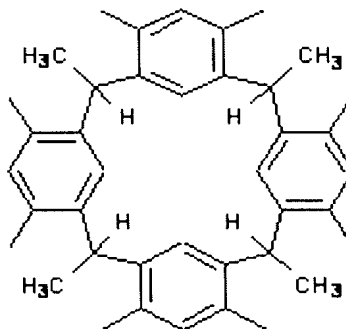
Claim 41 (Previously Presented): The photoresist composition according to claim 35, wherein at least one of B, C, and D is a hydrogen atom and X, Y, and Z are ether bonds.

Claim 42 (Previously Presented): The photoresist composition according to claim 35, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.

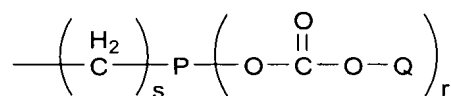
Claim 43 (New): A photoresist composition comprising a photoresist base material that is an extreme ultraviolet radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by the following formula,



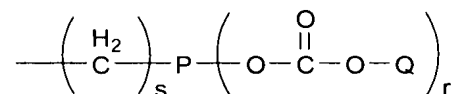
B, C, and D are individually an organic group shown by formula,



wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, or an organic group represented by any of the following formulas,



wherein Ar is a phenyl group or a naphthyl group substituted with RO- and/or ROCO-, wherein R is a tert-butyl group, tert-butyloxycarbonylmethyl group, tert-butyloxycarbonyl group, 1-tetrahydropyranyl group, 1-tetrahydrofuranyl group, 1-ethoxyethyl group, 1-phenoxyethyl group, or an organic group shown by the following formula,



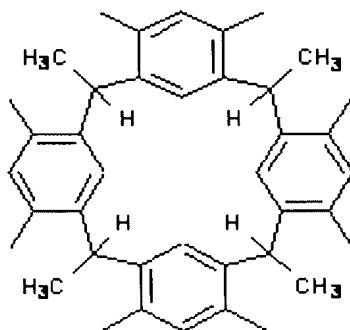
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10,

X, Y, and Z individually represent a single bond or an ether bond, and

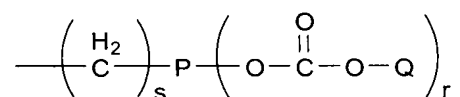
$$1 + m + n = 8.$$

Claim 44 (New): The photoresist composition according to claim 43, wherein the extreme ultraviolet-radiation reactive organic compound is in an amorphous state at room temperature and the average diameter of the molecule is 2 nm or less.

Claim 45 (New): The photoresist composition according to claim 43, wherein A is the organic group represented by the following formula,



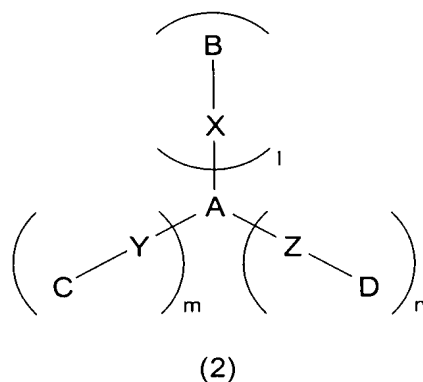
B, C, and D are individually an organic group shown by the following formula,



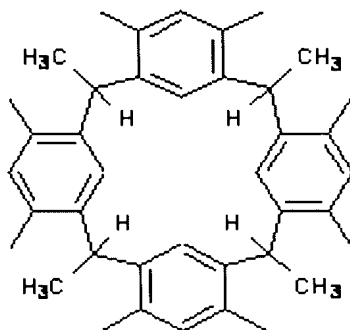
wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10, and

X, Y, and Z are ether bonds.

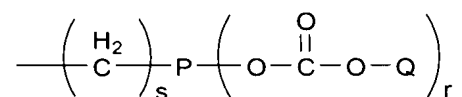
Claim 46 (New): A photoresist composition comprising a photoresist base material that is a radiation-reactive organic compound shown by formula (2), obtained by washing with an acidic aqueous solution and processing with an ion-exchange resin, a photoacid generator or a photobase generator, and a quenching agent,



wherein A is an organic group represented by the following formula,



B, C, and D are individually an organic group shown by formula,

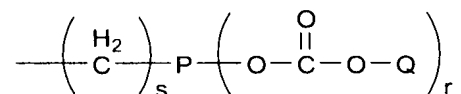


wherein P is an aromatic group having 6 to 20 carbon atoms with a valence of (r + 1), Q represents an organic group having 4 to 30 carbon atoms, r is an integer of 1 to 10, and s is an integer of 0 to 10,

X, Y, and Z individually represent a single bond or an ether bond, and

$$1 + m + n = 8.$$

Claim 47 (New): The photoresist composition according to claim 46, wherein the organic group shown by the following formula,



is a 4-(tert-butoxycarbonyloxy)benzyl group or a 3,5-di(tert-butoxycarbonyloxy)benzyl group.

Claim 48 (New): The photoresist composition according to claim 46, wherein the radiation is extreme ultraviolet radiation or an electron beam.

Claim 49 (New): The photoresist composition according to claim 46, wherein the basic impurity content of the photoresist base material is not more than 10 ppm.